

AMENDMENTS TO THE SPECIFICATION

Please replace paragraph [0067] and the preceding line with the following amended paragraph:

Example 3 (Comparative Example 1)

[0067] A device was fabricated in the same manner as in Example 1 except that the hole-injection layer of HAT was not formed. The resulting structure of the device was represented as “Glass substrate/ITO(1300 Å)/Al(100 Å)/Al₂O₃(20 Å)NPB(400 Å)/Alq3(300 Å)/Formula II(200 Å)/LiF(10 Å)/Al(2500 Å).” No emission was observed even when applying over 20 V forward bias to the device. The current density during the application of the forward bias was less than 0.1 mA/cm².

Please replace paragraph [0068] the preceding line with the following amended paragraph:

Example 4 (Comparative Example 2)

[0068] A device was fabricated in the same manner as in Example 1 except that the aluminum and aluminum oxide layers between the ITO and NPB were not formed. The resulting structure was represented as “Glass substrate/ITO(1300 Å)/HAT(500 Å)/NPB(400 Å)/Alq3(300 Å)/Formula 11(200 Å)/LiF(10 Å)/Al(2500 Å).” When 5.37 V of forward bias was applied across the resulting device, green emission of the color x=0.345, y=0.553 of the 1931 CIE color coordination was observed. The current density during the operation was 50 mA/cm². At 100 mA/cm² of constant DC current density, it took 23 hours until the brightness drops to 80% level of the initial brightness of 3399 nit.

Please replace paragraph [0074] the preceding line with the following amended paragraph:

Example 8 (Comparative Example 3)

[0074] A device was fabricated in the same manner as in Example 7 except that 1600 Å thickness of NPB was formed instead of HAT. The resulting structure of the device was represented as “Glass substrate/ITO(1300 Å)/NPB(1600 Å)/A1(500 Å).” When a forward bias was applied across the device, electric current was observed at a potential difference about 1 V. The voltage-current relationship was also shown in Figure 10.

Please replace paragraph [0076] the preceding line with the following amended paragraph:

Example 10 (Comparative Example 4)

[0076] A device was fabricated in the same manner as in Example 9 except that 2000 Å thickness of NPB was formed instead of HAT. The resulting structure of the device was represented as “Glass substrate/A1(500 Å)/NPB(2000 Å)/A1(500 Å).” When a forward bias was applied across the device, no electric current was observed even at a potential difference over 20 V. The voltage-current relationship was also shown in Figure 11.

Please replace paragraph [0078] the preceding line with the following amended paragraph:

Example 12 (Comparative Example 5)

[0078] To the device fabricated in the Example 10 having the construction of “Glass substrate/A1(500 Å)/NPB(2000 Å)/A1(500 Å),” an electric potential was applied with the opposite polarity to that of Example 10, in which the aluminum located between the glass substrate and NPB layer acted as a cathode, and the aluminum located above the HAT acted as an anode. When the forward bias was applied, almost no current was observed at a potential difference of above 20V. The voltage-current relationship was also shown in Figure 12.